Rashba Effect in the TI-induced (1×1) and (3×1) Structures on Ge(111)

The electronic structure and spin splitting caused by the Rashba spin-orbit (SO) coupling were investigated for the (1×1) and (3×1) structures on the Tl/Ge(111) surface by angle-resolved photoelectron spectroscopy (ARPES) and a first-principles band calculation. In the calculations with the SO interaction taken into account, the surface states with Tl 6p character show spin splitting. While the corresponding states were observed by ARPES, the spin splitting could not be confirmed due to the limited energy resolution. The largest splitting of ~700 meV is found for the lowest unoccupied states on the (1×1) surface. The wavefunction amplitude of the spin-split states is concentrated at the level of Tl, indicating that the heavy core potential of Tl is important for a large Rashba effect.

The Rashba spin-orbit (SO) interaction in twodimensional electron systems has become a hot topic in both surface and semiconductor science in recent years. The SO interaction originates from the potential gradient normal to the surface (∇y) and is described by

 $H = \frac{\hbar}{4m^2 c^2} \vec{\nabla} \cdot (\vec{\nabla} V \times \vec{p})$ [1,2] for two-dimensional free

electrons, where $\vec{\sigma}$ and \vec{p} are the Pauli spin operator and the electron momentum, respectively. The SO interaction causes spin-split states on a non-magnetic substrate without an external magnetic field, which could provide an important advantage for future applications in spintronics. The Rashba spin splitting in surface states was first observed on Au(111) [3]. A larger splitting, of the order of 1 eV was observed for both low-index Bi surfaces and Bi-induced structures on Ag surfaces [4-6]. The free-electron model cannot explain these large splittings, and the heavy core potential is considered to be important for understanding the spin splitting in surface states. In order to investigate the SO interaction on a semiconductor surface, we studied TI-induced (1× 1) and (3×1) structures on Ge(111) substrate by using angle-resolved photoelectron spectroscopy (ARPES) and a first-principles band calculation [7, 8]. On the (1 \times 1) surface, TI atoms are located at T₄ sites on bulktruncated Ge(111) (Fig. 1(a)). The (3×1) surface has a honeycomb-chain-channel structure, the common framework for alkali-metal-induced (3×1) structures on Si(111) and Ge(111), with TI residing on H_3 sites (Fig. 1(b)).



Atomic structure models of the (1×1) and (3×1) structures on TI/ Ge(111).



Figure 2 ARPES spectra of (a) TI/Ge(111)-(1×1) along TK with h_V =21.2 eV [6] and (b) TI/Ge(111)-(3×1) along TA with h_V =16 eV [7].

We carried out the ARPES experiments at BL-18A using photon energies hv=12, 16, 22, 40 eV, and at Kyoto University using hv=21.2 eV. The first-principles band calculation incorporating the SO interaction was performed with the WIEN2k computer code.

Figures 2 show ARPES spectra of the (1×1) and (3 \times 1) structures. A TI-induced bands S₁ and S₂ are found in the bulk-band gap on the respective surfaces. Figure 3(a) shows the calculated band structure of the (1×1) structure. The surface band structure is characterized by S_1 , the dangling-bond state on the topmost Ge, and U_1 , the TI–TI anti-bonding state. Although U_1 is partially occupied in the calculation with limited k-point sampling, the corresponding feature was not observed in ARPES. TI interacts with Ge(111) as a monovalent ion due to the inert-pair effect, and the TI-Ge bond has a strong ionic character. Similar behavior of TI is also seen on the (3×1) structure. The charge transfer from TI to Ge terminates the dangling bonds of the honeycomb chain Ge adatoms. The S_2 band in Fig. 3(b) is mainly derived from the dangling-bond state of the Ge adatom facing TI.





Figure 3

Calculated band structure of (a) the (1×1) and (b) the (3×1) structures on Tl/Ge(111). Also shown are the wavefunctions of (c) U_t and (d) U_s at \overline{K} and \overline{A} , respectively. The calculated surface bands show spin splittings of up to 150–700 meV. The calculated S_1 band shows a spin splitting of ~200 meV at around \overline{K} , which is probably responsible for the broadening of the S_1 feature from $\overline{\Gamma}$ to \overline{K} in Fig. 2(a). As to S_2 and U_2 , it is worth noting that the spin splitting of U_2 disappears at the middle of $\overline{A} - \overline{B}$ and \overline{C} . This behavior is consistent with the inhibition rule of the spin splitting due to the Rashba SO coupling. The splittings of U_1 and U_2 are relatively larger than those of S_1 and \overline{S}_2 . This difference is ascribed to the stronger TI 6p character of U_1 and U_2 . Figures 3(c) and (d) show the wavefunction distributions of the U_1 and U_2 states at \overline{K} and \overline{A} , respectively. The states at \overline{K} with the largest splitting of ~700 meV have purely TI 6p,+6p, character and are strongly localized at the TI layer.

In conclusion, we found on TI/Ge(111) large spin splittings of the surface states due to the Rashba SO coupling. The dominant TI 6p contribution to the lowest unoccupied states causes the large spin splittings.

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BEAMLINE

18A

S. Hatta^{1,2}, C. Kato¹, S. Takahashi¹, A. Harasawa³, T. Okuda³, T. Kinoshita³, H. Okuyama¹ and T. Aruga^{1,2} (¹Kyoto Univ., ²JST CREST, ³The Univ. of Tokyo)

PF Activity Report 2007 #25

An *In Situ* Photoemission Study of Pr_{1-x}Ca_xMnO₃ Epitaxial Thin Films with Suppressed Charge Ordering

When have performed an in situ photoemission study of $Pr_{1,2}Ca_{A}MnO_{3}$ thin films grown on LaAIO₃ (001) substrates and observed the effect of epitaxial strain on the electronic structure. The band dispersions determined by angle-resolved photoemission spectroscopy showed that the films were insulators. The dispersions could not be explained by the metallic band structure of the C-type anti-ferromagnetic state, where spins are coupled antiferromagnetic chain direction or due to another type of spin-orbital ordering. We observed a doping-induced chemicalpotential shift toward the Fermi level (E_{E}) with hole doping, but no spectral weight transfer near E_{E} . These results can be explained by the suppression of charge ordering and charge fluctuations due to compressive strain from the substrate.

Hole-doped perovskite manganese oxides $R_1 A_2 MnO_3$, where R is a rare-earth (R = La, Nd, Pr) and A is an alkaline-earth atom (A = Sr. Ba. Ca), have attracted much attention because of their remarkable physical properties such as colossal magnetoresistance and ordering of spin, charge, and orbitals [1]. Most of the half-doped manganites (x = 0.5) with small bandwidths exhibit the so-called "CE-type" anti-ferromagnetic (AF) charge ordering (CO), with alternating Mn3+ and Mn⁴⁺ states within the (001) plane in the form of stripes [2]. Pr1-xCaxMnO3 (PCMO), which has the narrowest bandwidth, has a particularly stable CO state with a wide hole concentration range between x = 0.3 and 0.75 [3]. In this work, we have used photoemission spectroscopy to study the electronic structure of PCMO thin films grown on LaAIO₃ (LAO) substrates [4]. The substrates create a compressive strain on the films, which is expected to suppress CO and charge fluctuations [5].

Epitaxial thin films of PCMO with thicknesses of about 40 nm were fabricated using the pulsed laser deposition method. Single crystals of LAO (001) were used as the substrates. The in-plane lattice constants of the PCMO thin films were the same as those of LAO (a = 3.792 Å), confirming epitaxial and coherent growth of the thin films on the substrates. For all compositions, the out-of-plane lattice constants were longer than the in-plane lattice constants, indicating that the PCMO thin films were under compressive strain. The photoemission measurements were performed at BL-1C and 2C, using a combined laser molecular-beam epitaxy and photoemission spectrometer system [6]. The photoemission spectra were recorded using a Gammadata Scienta SES-100 spectrometer with the total energy resolution set to about 150 - 400 meV depending on photon energy. All spectra were recorded at room temperature, except for the angle-resolved photoemission spectroscopy (ARPES) measurements which were performed at 20 K.



Figure 1

26 Highlights

Comparison of the ARPES spectra measured in normal-emission geometry with a tight-binding band structure calculation. The bright parts correspond to energy bands. (a) Experimental band structure of PCMO (x = 0.4). (b) Tight-binding calculation of the C-type AF state.



Figure 2 Schematic illustration of the electronic structures of PCMO for bulk and thin film samples.

Figure 1 shows the normal-emission ARPES spectra (out-of-plane band dispersions) of PCMO (x=0.4) (a), and tight-binding band-structure calculations of the previously proposed C-type AF state (b). The strong dispersion of the Mn 3d e, bands predicted by the calculation (enclosed by a blue rectangle in Fig. 1 (b)) was not observed in the experiment. The e_a electrons appear to be localized along the ferromagnetic chain direction due to disorder and/or electron correlation. In the valence band, we observed an energy shift of the spectra which is attributed to the effect of the chemicalpotential shift. No new states appeared near the Fermi level (E_F) due to hole doping. This result is in contrast with the results for bulk PCMO, where spectral weight transfer from high to low energies occurs near E_F due to hole doping [7]. From the present results, we conclude that our PCMO thin films were good insulators with no dynamical "phase separation." The suppression of incommensurate charge fluctuations is due to the compressive strain effects from the LAO substrates. This difference in electronic structure between the bulk and thin film samples is shown schematically in Fig. 2. In the bulk samples, there is a macroscopic and/or microscopic (one-dimensional stripe type) phase separation, but in the thin film samples with in-plane compressive strain, PCMO behaves as a homogeneous complete insulator.

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BEAMLINE 1C and 2C

H. Wadati^{1, 2}, A. Maniwa¹, A. Chikamatsu¹, I. Ohkubo¹, H. Kumigashira^{1, 3}, M. Oshima^{1, 3}, A. Fujimori¹, M. Lippmaa⁴, M. Kawasaki^{3, 5} and H. Koinuma^{1, 6} (¹Univ. of Tokyo, ²UBC, ³CREST-JST, ⁴ISSP, ⁵Tohoku Univ., ⁶NIMS)

Estimate of the Time Constant for Proton Transfer between Water and Hydroxyl on a Pt(111) Surface

The time scale of proton transfer between H₂O and OH on a Pt(111) surface was measured using a combination of laser-induced thermal desorption (LITD) and micro-scale X-ray photoelectron spectroscopy (micro-XPS). A one-dimensional patterned distribution OH + H₂O/H₂O/OH + H₂O was initially prepared on the Pt(111) surface by LITD, and the time evolution of the spatial distribution of OH and H₂O was measured using micro-XPS. From quantitative analyses based on a diffusion equation, we found two proton-transfer pathways with time constants at 140 K of 5.2 ± 0.9 ns and 48 ± 12 ns. The two pathways were respectively attributed to direct proton transfer to the neighboring site, and H₃O⁺-mediated transfer to the next-nearest site.

Proton transfer in hydrogen-bonded systems is a fundamental natural process and plays a significant role in many physical, chemical, and biological processes. Knowledge of the time scale on which the proton transfer occurs is essential for the understanding of these processes, although it is not always straightforward to determine the transfer rate experimentally. On a Pt(111) surface. OH and H₂O molecules form a well-ordered two-dimensional (2D) mixed honevcomb structure. The OH + H₂O mixed phase has previously been observed during water formation from oxygen and hydrogen on a Pt(111) surface [1], and it has been suggested that proton transfer in the mixed phase plays a crucial role in promoting the autocatalytic reaction [2]. Proton transfer in the mixed structure was also suggested by studies using density functional theory [3] and infrared absorption reflection spectroscopy [4]. However the time scale of the proton transfer in this 2D hydrogenbonding network was until now unknown. In this work we have estimated experimentally the time scale of the proton transfer from H₂O to OH in the mixed phase on a Pt(111) surface [5].

The experiments were performed at BL-7A under ultrahigh vacuum conditions. As shown in Fig. 1(a), a one-dimensional (1D) spatial distribution OH+H₂O/H₂O/OH+H₂O was prepared by scanning a pulsed Nd:YAG laser beam along one direction on the mixed OH + H₂O overlayer to make a 400 μ m wide 1D vacant band, with subsequent filling of the vacant area by H₂O molecules. The coverage distribution changes of OH and H₂O were monitored using micro-XPS with a spatial resolution of 16.5 μ m at 140 K.

Figure 1(b) shows the micro-XPS image obtained for the initial distribution. The coverage distributions for OH and H_2O were determined at different elapsed times by fitting to standard spectra, the results of which are shown in the top part of Fig. 2. In the central region, OH coverage increases over time while H_2O coverage decreases. Because OH does not diffuse at 140 K [1], it can be deduced that the OH observed in the central region results from proton transfer between H_2O and OH.

800

(b)



Figure 1

(a)





Figure 2

($\overline{\text{Op}}$) Coverage distributions of OH and H₂O at the 1D patterned structure at different elapsed times. (Bottom) Schematics of the two proton transfer processes: (a) simple proton transfer and (b) proton transfer via H₃O⁺. The probabilities of the two processes are shown as a function of the coverage.

From the observed distribution changes, we estimated the rate of proton transfer based on a diffusion equation considering two pathways. The first process is simple proton transfer from H₂O to a neighboring OH, as shown in Fig. 2(a). The second process is H₃O⁺-mediated proton transfer, as shown in Fig. 2(b). From fitting analyses using the diffusion equation, the time constant of the simple proton transfer process was found to be 5.2 \pm 0.9 ns, and that of the H₃O⁺-mediated process to be 48 ± 12 ns. These time constants are intermediate to those which occur for liquid and 3D-solid phases, which relates to the degrees of freedom available for proton transfer. We also checked for any solvent effects on the 2D proton transfer by performing spatio-temporal tracing of the OH+H2O/H2O/OH+H2O overlayer under water multilayers at 140 K, and observed a significant reduction in proton transfer rate in the 2D hydrogenbonding network. This suggests peripatetic behavior of the protons, with transfer to H₂O molecules in the upper layer. The understanding of proton dynamics at 2D

interfaces will be important for understanding protonics at interfaces such as fuel-cell electrodes and biological membranes.

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BEAMLINE

M. Nagasaka^{1,2}, H. Kondoh^{1,3}, K. Amemiya^{1,4}, T. Ohta^{1,5} and Y. Iwasawa¹ (¹The Univ. of Tokyo, ²IMS, ³Keio Univ., ⁴KEK-PF, ⁵Ritsumeikan Univ.)

28 Highlights

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CO Adsorption Effects on the Magnetism of Fe/Cu(001) Thin Films

O adsorption effects on the magnetism of Fe films on Cu(001) were studied at 100 K as a function of film thickness. It was found that CO adsorption does not affect the magnetic properties of a 2 ML Fe film, but induces spin reorientation from out-of-plane to in-plane magnetization for 3 and 4 ML films. It also causes a decrease in overall magnetization, which can be attributed to a reduction in surface magnetization. Possible origins of these complicated magnetic behaviors are discussed.

The atomic and magnetic properties of Fe thin films on Cu(001) have been extensively studied as prototypical cases of magnetic thin films[1]. Fe/Cu(001) films exhibit three characteristic regimes; regimes I (< 4 ML), II (5-11 ML), and III (> 12 ML). Here we focus on regime I, which exhibits a distorted fcc structure and a ferromagnetic coupling throughout the whole film with perpendicular magnetization.

In this article, we report on the effects of CO adsorption on the magnetism of Fe/Cu(001) films [2]. Films with 2 ML Fe are not affected, but 4 ML films show drastically changed magnetic properties following adsorption, with the direction of magnetization rotating from perpendicular to in-plane, and the two surface layers losing their spin magnetic moment.

The experiments were performed at BL-7A and BL-11A, which are equipped with an ultrahigh vacuum chamber. Fe/Cu(001) films were prepared in the chamber at room temperature. Conventional and depth-resolved X-ray magnetic circular dichroism (XMCD) measurements [3] were carried out at 100 K with normal (90°) and grazing (30°) X-ray incidence, hereafter referred to

as "NI" and "GI". After measurements of the bare films, each film was dosed with 5 L of CO and the measurements repeated.

The Fe *L*-edge XMCD spectra of Fe(2 and 4 ML)/ Cu(001) are shown in Figs. 1(a) and (c). The spectra are quite similar, revealing perpendicular magnetization with spin magnetic moments of about $m_s = 2.4 \mu_{\rm B}$ for both films.

Next we discuss the effects of CO adsorption on the films. Fe *L*-edge XMCD spectra of CO-adsorbed 2 and 4 ML Fe films are shown in Figs. 1 (b) and (d). The XMCD spectra of CO/Fe(2 ML)/Cu(001) are essentially the same as those of Fe(2 ML)/Cu(001): CO adsorption does not affect the XMCD spectra of the 2 ML Fe film. In contrast, the XMCD spectra of CO/Fe(4 ML)/Cu(001) exhibit almost no signal for NI geometry, with significant signal only for GI geometry. These features directly indicate the in-plane magnetization of the film. Thus it can be concluded that CO adsorption rotates the easy axis of magnetization of the 4 ML film from perpendicular to in-plane.



Figure 1

Fe L-edge XMCD spectra of the 2 ML Fe film before (a) and after (b) CO adsorption. The same spectra for the 4 ML Fe film are shown in (c) and (d). The blue spectra represent XMCD spectra for NI geometry and the red spectra those for GI geometry.



Probing depth dependence of the Fe effective spin magnetic moment, m_g of CO/Fe(4 ML)/Cu(001), along with the schematic model. The crosses represent experimentally obtained moments, and the solid red line a fit with (m_{wa}, m_w) = (0.17, 2.31) µ_B.

The spin magnetic moment obtained for CO/Fe(4 ML)/Cu(001) of $1.1\mu_{\rm B}$ is about half the magnitude of that of CO/Fe(2 ML)/Cu(001) (2.3 $\mu_{\rm B}$). This apparent decrease in $m_{\rm s}$ is considered to be due to the disappearance of the contributions to $m_{\rm s}$ of the top two layers. The depth-resolved XMCD spectra give us the probing depth (effective electron escape depth) dependence of $m_{\rm s}$, shown in Fig. 2. The spin magnetic moment decreases with decreasing probe depth, directly showing that the moment is small near the surface. The plot shown in Fig. 2 was analyzed with a simple model, composed of the top two layers and bottom two layers, also shown in Fig. 2. The top two layers have little magnetic moment (0.17 $\mu_{\rm B}$), while the bottom two layers exhibit a moment of 2.31 $\mu_{\rm B}$.

In summary, the effects of CO adsorption on the magnetism of Fe(2 and 4 ML)/Cu(001) were studied at 100 K. The 2 ML film was not affected by CO adsorption. In contrast, the 4 ML Fe films changed their magnetism drastically, with the direction of magnetization rotating from perpendicular to in-plane. In addition, the two surface layers lose their spin magnetic moment upon CO adsorption, and consequently the bottom two layers show magnetization. These complex magnetic phases can be interpreted by assuming that CO adsorption kills the ferromagnetic coupling of the surface layers while the Cu(001) substrate always maintains ferromagnetic coupling with the adjacent two layers.

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BEAMLINE 7A and 11A

H. Abe¹, K. Amemiya², D. Matsumura³, J. Miyawaki⁴, E.O. Sako², T. Ohtsuki⁵, E. Sakai⁵ and T. Ohta⁶ (¹Keio Univ., ²KEK-PF, ³JAEA, ⁴Riken Harima Inst., ⁵The Univ. of Tokyo, ⁶SR Center, Ritsumeikan Univ.)